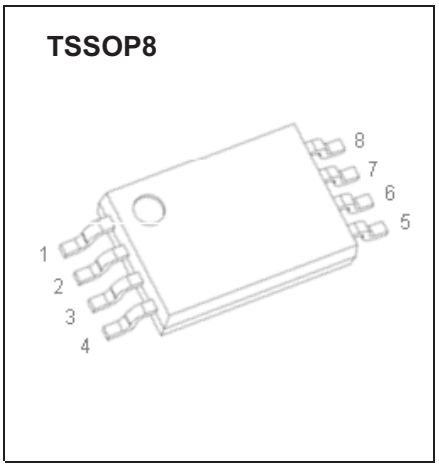
JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD

TSSOP8 Plastic-Encapsulate MOSFETS

CJS9004 Dual N-Channel MOSFET

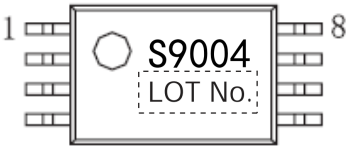


$V_{(BR)DSS}$	$R_{DS(on)}$TYP	I_D
20V	7.5mΩ@4.5V	10A
	8.0mΩ@4.0V	
	8.4 mΩ@3.8V	
	8.9 mΩ@3.1V	
	9.7 mΩ@2.5V	

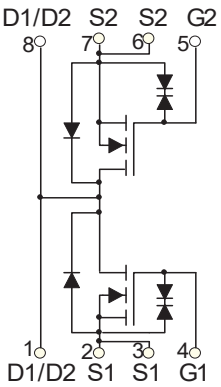
DESCRIPTION

The CJS9004 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. It is ESD protected. This device is suitable for use as a uni-directional or bi-directional load switch,facilitated by its common-drain configuration.

MARKING:



Equivalent Circuit



MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current	I_D	10	A
Pulsed Drain Current	I_{DM}*	50	A
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	62.5	℃/W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55~+150	℃
Lead Temperature for Soldering Purposes(1/8'' from case for 10 s)	T_L	260	℃

MOSFET ELECTRICAL CHARACTERISTICS

T_a=25℃ unless otherwise specified

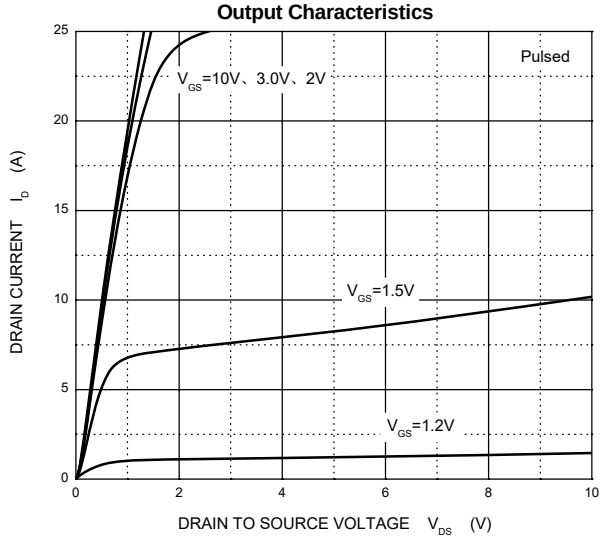
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	20			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =16V,V_{GS} = 0V			1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±4.5V, V_{DS} = 0V			±1	μA
		V_{GS} =±8V, V_{DS} = 0V			±10	μA
Gate threshold voltage (note 1)	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	0.5	0.7	0.9	V
Drain-source on-resistance (note 1)	$R_{DS(on)}$	V_{GS} =4.5V, I_D =3A	6.0	7.5	9.0	mΩ
		V_{GS} =4.0V, I_D =3A	7.0	8.0	9.5	mΩ
		V_{GS} =3.8V, I_D =3A	7.5	8.4	9.8	mΩ
		V_{GS} =3.1V, I_D =3A	8.0	8.9	10	mΩ
		V_{GS} =2.5V, I_D =3A	9.0	9.7	12	mΩ
Forward tranconductance (note 1)	g_{FS}	V_{DS} =5V, I_D =7A	8	23		S
Diode forward voltage(note 1)	V_{SD}	I_S=1A, V_{GS} = 0V		0.7	1	V
DYNAMIC PARAMETERS (note 2)						
Input Capacitance	C_{iss}	V_{DS} =10V,V_{GS} =0V,f =1MHz		1040		pF
Output Capacitance	C_{oss}			225		pF
Reverse Transfer Capacitance	C_{rss}			195		pF
Total gate charge	Q_g	V_{DS} =10V,V_{GS} =4.5V,I_D =7A		13		nC
Gate-source charge	Q_{gs}			2.8		nC
Gate-drain charge	Q_{gd}			5.6		nC
SWITCHING PARAMETERS(note 2)						
Turn-on delay time	$t_{d(on)}$	V_{GS}=5V,V_{DD}=10V, R_L=1.35Ω,R_{GEN}=3Ω		28		ns
Turn-on rise time	t_r			64		ns
Turn-off delay time	$t_{d(off)}$			90		ns
Turn-off fall time	t_f			58		ns
Drain-Source Diode Characteristics						
Diode Forward Current	I_S		-	-	6.0	A

Notes :

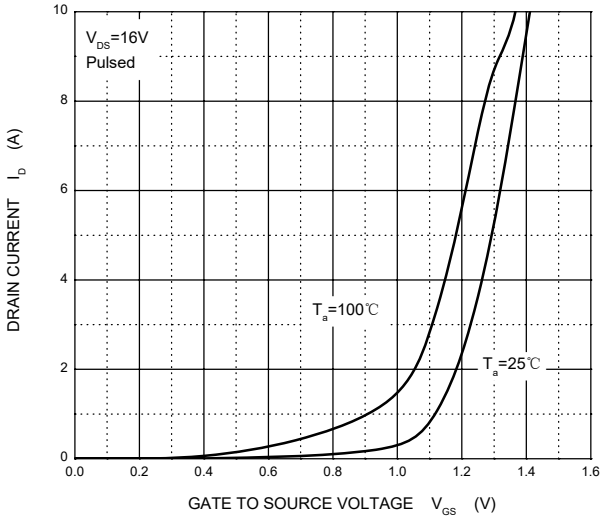
1. Pulse Test : Pulse width≤300μs, duty cycle≤0.5%.
2. Guaranteed by design, not subject to production testing.

Typical Characteristics

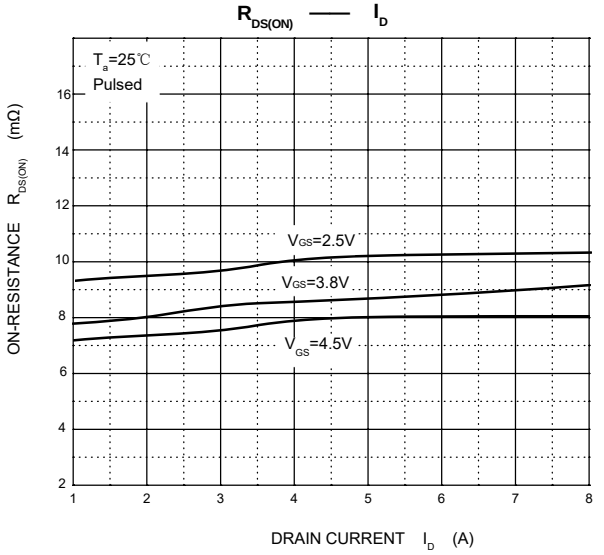
Output Characteristics



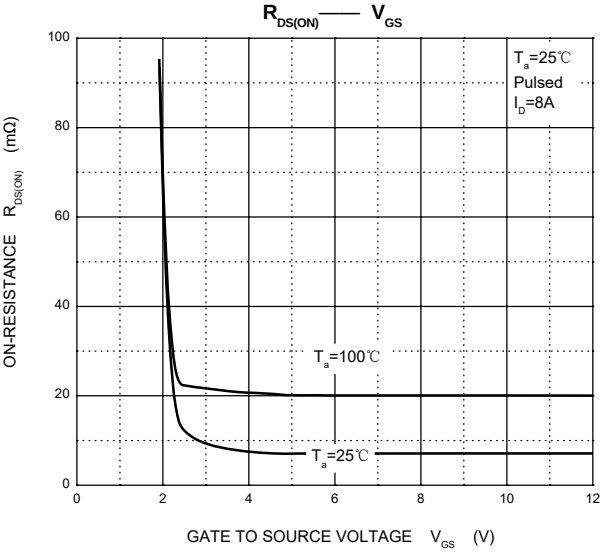
Transfer Characteristics



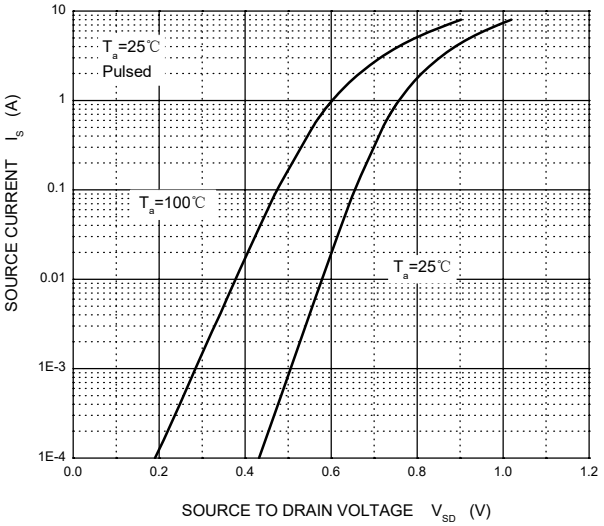
$R_{DS(ON)}$ —— I_D



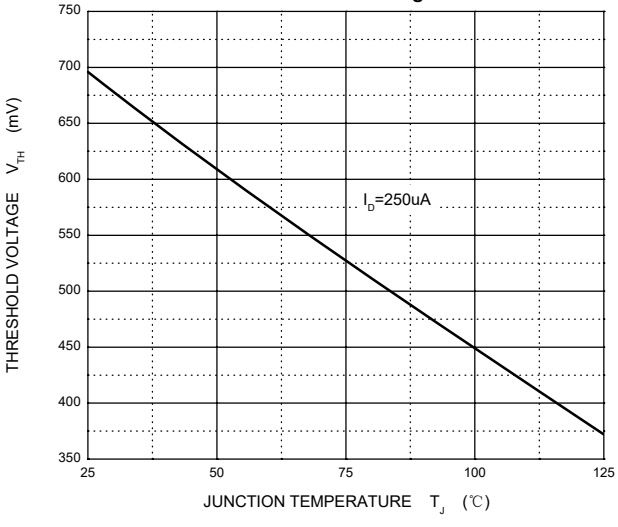
$R_{DS(ON)}$ —— V_{GS}



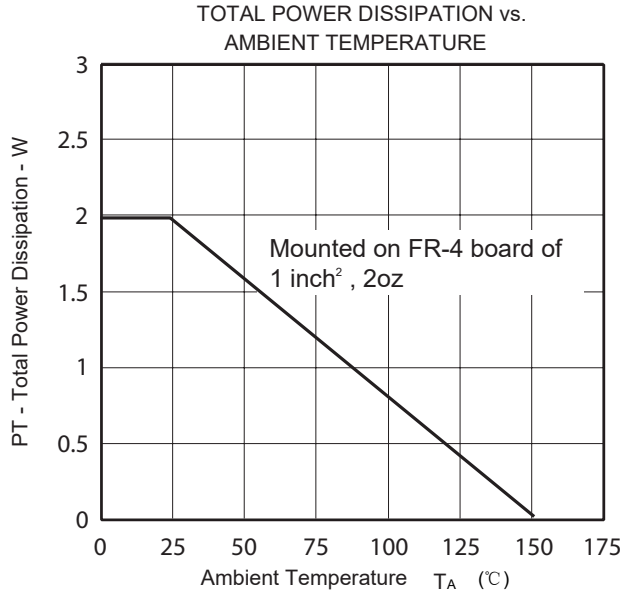
I_S —— V_{SD}

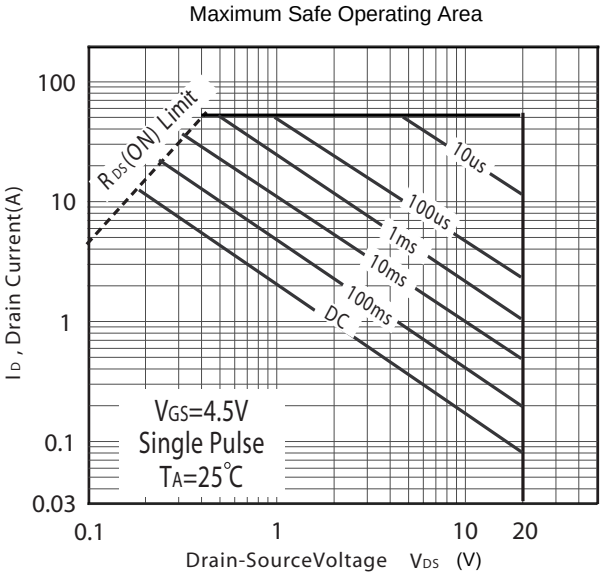


Threshold Voltage

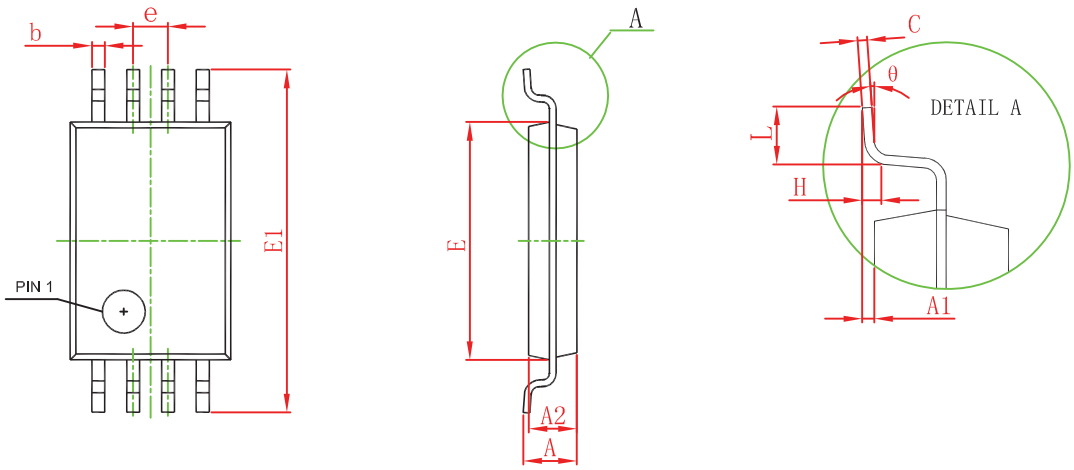


Typical Characteristics



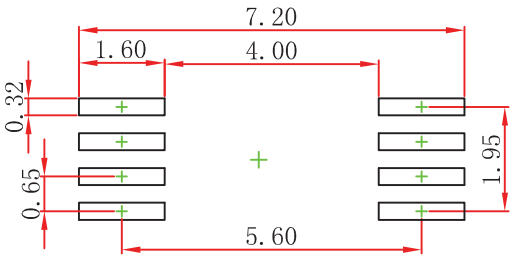


TSSOP8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	**Max**	**Min**	**Max**
D	2. 900	3. 100	0. 114	0. 122
E	4. 300	4. 500	0. 169	0. 177
b	0. 190	0. 300	0. 007	0. 012
c	0. 090	0. 200	0. 004	0. 008
E1	6. 250	6. 550	0. 246	0. 258
A		1. 200		0. 047
A2	0. 800	1. 000	0. 031	0. 039
A1	0. 050	0. 150	0. 002	0. 006
e	0. 65 (BSC)		0. 026 (BSC)	
L	0. 500	0. 700	0. 020	0. 028
H	0.25(TYP		0.01(TYP	
θ	1°	7°	1°	7°

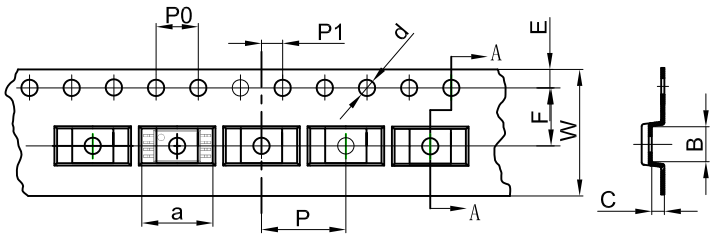
TSSOP8 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

TSSOP8 Tape and Reel

TSSOP8 Embossed Carrier Tape



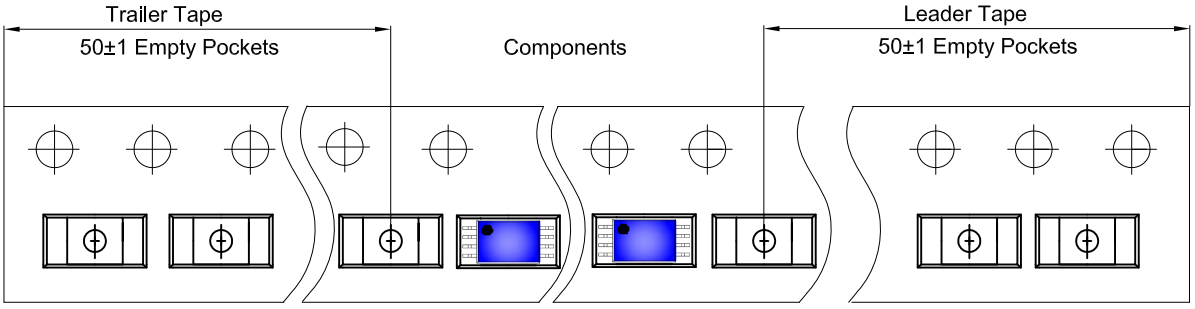
Packaging Description:

TSSOP8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

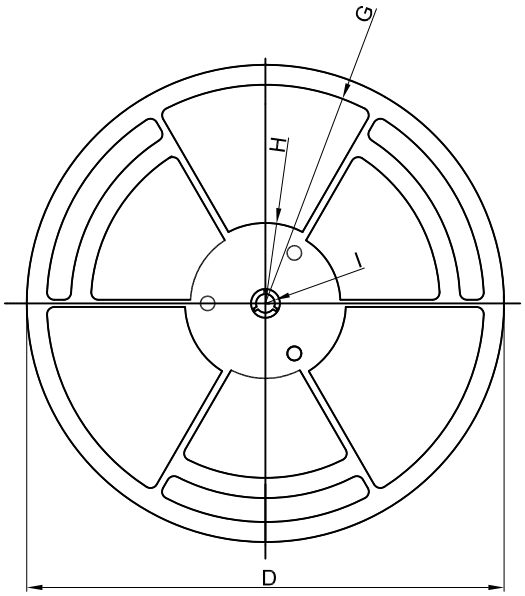
ALL DIM IN mm

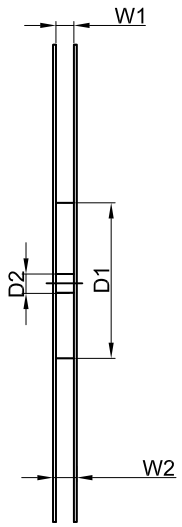
Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
TSSOP8	6.76	3.30	1.20	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

TSSOP8 Tape Leader and Trailer



TSSOP8 Reel





Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
13"Dia	Ø330.00	100.00	13.00	R151.00	R56.00	R6.50	12.40	17.60

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3,000 pcs	13 inch	3,000 pcs	336×336×48	24,000 pcs	445×355×365	

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